Abstracts

A single-bias diode-regulated 60 GHz monolithic LNA

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This paper presents a small-size 60 GHz-band GaAs MMIC LNA with a single bias supply. A diode-regulated self-bias circuit was proposed and demonstrated for suppressing the FET drain current variations due to threshold voltage nonuniformities. The developed three-stage MMIC LNA exhibited an average noise figure of 3.3 dB with 18 dB gain from 58 to 62 GHz. The chip size of the LNA is 1.85 mm/spl times/1.07 mm/spl times/0.04 mm.

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